Product data sheet

1. General description

WMS30N250E is a high performance logic level N-channel MOSFET in PDFN3.3X3.3 package, which utilizes advanced Trench MOSFET technology to provide low $R_{\tiny DS(on)}$ and gate charge. It is designed and qualified in a wide range of industrial and consumer applications.



2. Features and benefits

- · High ESD sensitivity devices
- Advance High Cell Density Trench Technology
- Low R_{DS(on)} to Minimize Conduction Losses
- Low Capacitance to Minimize Switching Losses
- Optimized Gate Charge to Minimize Driver Losses
- 100% UIS Tested
- RoHS Compliant, Halogen Free and Lead Free

3. Applications

- DC-DC Converters
- BLDC Motor Control
- Load Switch
- Lithium-ion Battery Protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit	
Absolute	maximum rating		·					
V_{DS}	drain-source voltage				30		V	
V_{GS}	gate-source voltage				±20		V	
I _D	continuous drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]		19		Α	
P _{tot}	power dissipation	T _{mb} = 25 °C		14		W		
T _j	junction temperature			-55 to 150			°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static cha	aracteristics		·					
R _{DS(on)}	drain-source on-state	V _{GS} = 10 V, I _D = 14 A		-	14	25	mΩ	
	resistance	$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$		-	22	35	mΩ	
Dynamic (Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 14 A; V _{DS} = 15 V; V _{GS} = 10 V		-	11	-	nC	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1-3	S	source	8 7 6 5	D
4	G	gate		
5-8	D	drain	0 1 2 3 4	sym300 S

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method		•	Package issue date
WMS30N250E	PDFN3.3X3.3	WMS30N250EJ	Reel	5000	PDFN3.3X3.3N	22-Sep-2022

7. Marking

Table 4. Marking codes

Type number	Marking codes
WMS30N250E	3N250

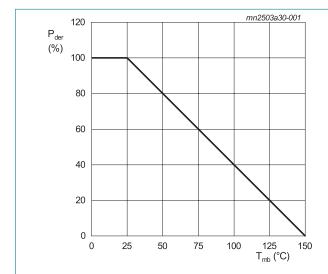
8. Limiting values

Table 5. Limiting values

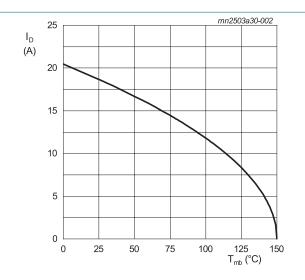
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DS}	drain-source voltage			30	V
V_{GS}	gate-source voltage			±20	V
I _D	continuous drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	19	Α
		V _{GS} = 10 V; T _{mb} = 120 °C		9.1	Α
I _{DM}	pulsed drain current	t _p = 10 μs; T _{mb} = 25 °C		76	А
P _{tot}	power dissipation	T _{mb} = 25 °C		14	W
E _{as}	single pulse drain-to- source avalanche	I_{AS} = 10 A; L = 0.1 mH; R_{GS} = 25 Ω ; V_{GS} = 10 V; T_{j} = 25 °C		5	mJ
T _{stg}	storage temperature			-55 to 150	°C
T _j	junction temperature			-55 to 150	°C

[1] Calculated continuous current based on maximum allowable junction temperature. Package current limitation is 14A.



P_{der} = (P_{tot} / P_{tot(25 °C)}) x 100% Fig. 1. Normalized total power dissipation as a function of mounting base temperature



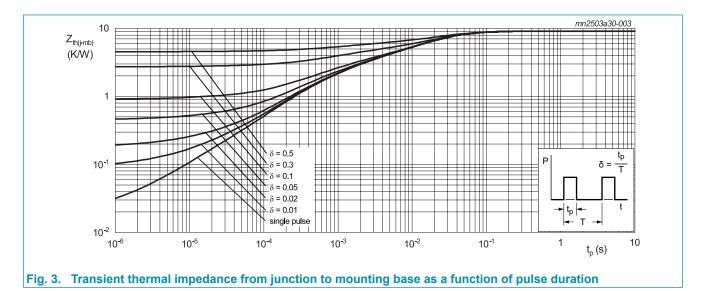
V_{GS} = 10 V
Fig. 2. Continuous Drain Current as a function of mounting base temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base			-	7	9.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[2]	-	-	60	K/W

[2] Surface mount on FR4 board of 1 inch², 1 oz copper.



10. Characteristics

Table 7. Characteristics

T_i = 25 °C unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics					'	
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V		30	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$		1.0	1.5	2.4	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C		-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	±100	nA
R _{DS(on)}	drain-source on-state	V _{GS} = 10 V; I _D = 14 A		-	14	25	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}$		-	22	35	mΩ
R _G	gate resistance	f = 1 MHz		-	2.4	-	Ω
Dynamic	characteristics						
Q _{G(tot)}	total gate charge	I _D = 14 A; V _{DS} = 15 V; V _{GS} = 10 V		-	11	-	nC
Q _{GS}	gate-source charge			-	2.2	-	nC
Q_{GD}	gate-drain charge			-	1.9	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz		-	552	-	pF
C _{oss}	output capacitance			-	71	-	pF
C _{rss}	reverse transfer capacitance			-	54	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}; R_G = 6 \Omega;$		-	2.6	-	ns
t _r	rise time	I _D = 14 A		-	4.9	-	ns
$t_{\text{d(off)}}$	turn-off delay time			-	7.1	-	ns
t _f	fall time			-	1.7	-	ns
Source-di	rain diode						
V _{SD}	source-drain voltage	V _{GS} = 0 V; I _S = 1 A		-	0.76	1	V
		V _{GS} = 0 V; I _S = 1 A; T _j = 125 °C		-	0.61	-	V
Is	body-diode continuous current	T _{mb} = 25 °C		-	-	15	Α
t _{rr}	reverse recovery time	$V_{GS} = 0 \text{ V}; I_S = 14 \text{ A}; \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		-	12	-	ns
Q _{rr}	reverse recovered charge			-	4.9	-	nC
I _{rrm}	reverse recovery current			-	0.6	-	Α

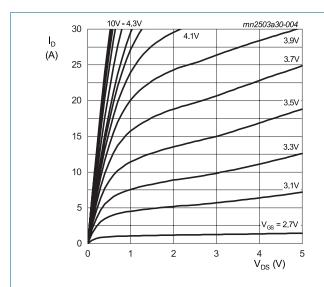
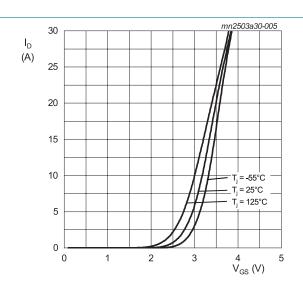
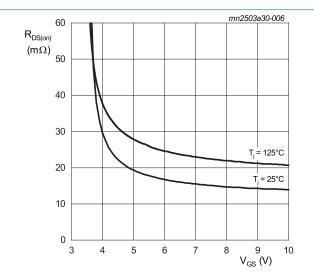


Fig. 4. Drain current as a function of drain-source voltage; typical values



V_{DS} = 5 V

Fig. 5. Drain current as a function of gate-source voltage; typical values



I_D = 14 A
Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

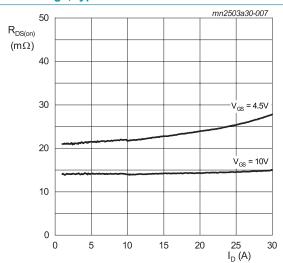
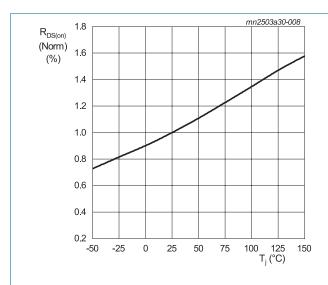
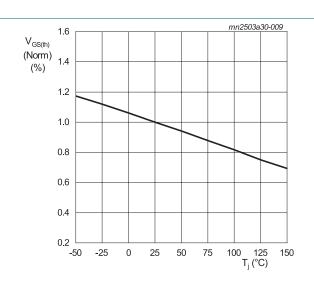


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



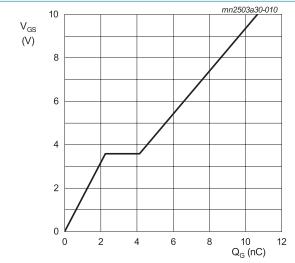
 V_{GS} = 10 V; I_{D} = 14 A

Fig. 8. Normalized drain-source on-state resistance as a function of junction temperature

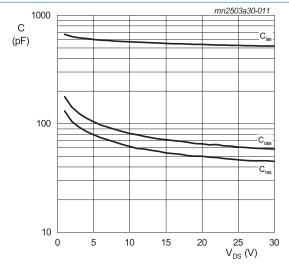


 $V_{DS} = V_{GS}$; $I_D = 250 \mu A$

Fig. 9. Normalized gate-source threshold voltage as a function of junction temperature



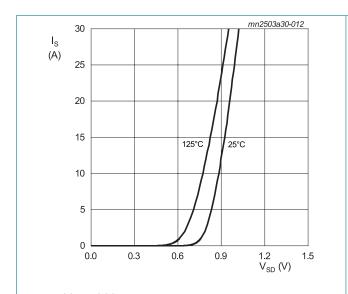
I_D = 14 A; V_{DS} = 15 V Fig. 10. Gate-source voltage as a function of gate charge; typical values



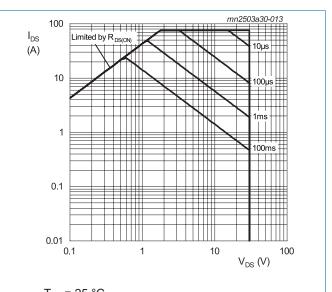
 V_{GS} = 0 V; f = 1 MHz Fig 11. Capacitances as a function of drain-source

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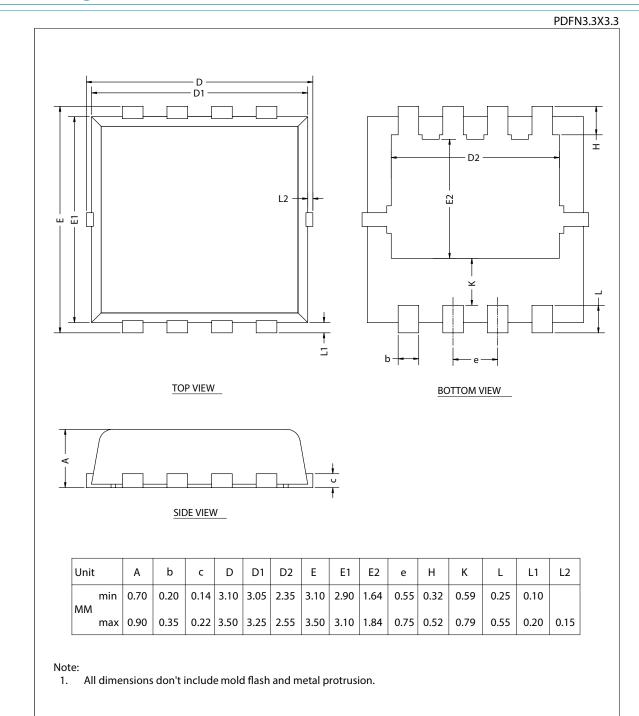


V_{GS} = 0 V
Fig 12. Source current as a function of source-drain voltage; typical values



 T_{mb} = 25 °C Fig. 13. Safe operating area

11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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